● General Description

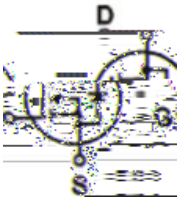
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

Trench technology

$_{DS(ON)}$ to minimize conductive loss

● Product Summary



V_{DS} =30V

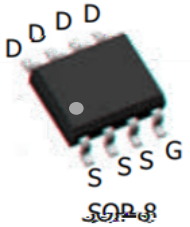
$R_{DS(ON)}$=20mΩ

I_D =6.8A

●Application

Load Switches

DC/DC



●Ordering Information:

Part NO.	ZM200N03S
Marking	ZM200N03H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

●Absolute Maximum Ratings T_C =25

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}T_C$=25	6	A
	$I_{D@}T_C$=75	4.5	A
	$I_{D@}T_C$=100	3.8	A
Pulsed Drain Current	I_{DM}	15	A
Total Power Dissipation	$P_D@T_C$=25	3.4	W
Total Power Dissipation	$P_D@T_A$=25	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	12	mJ

Fig.1 Gate-Charge Characteristics

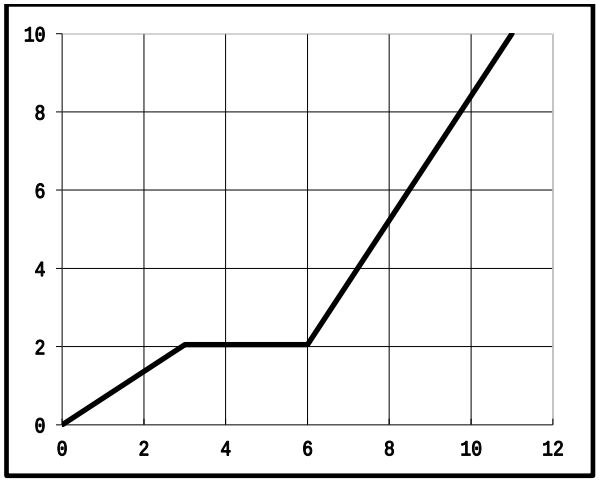


Fig.2 Capacitance Characteristics

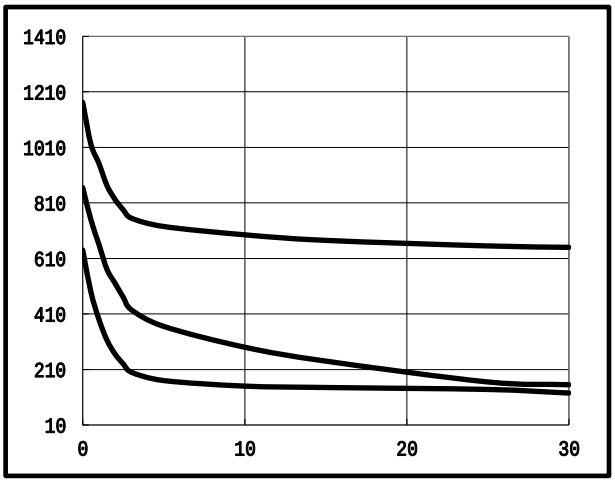


Fig.3 Power Dissipation Derating Curve

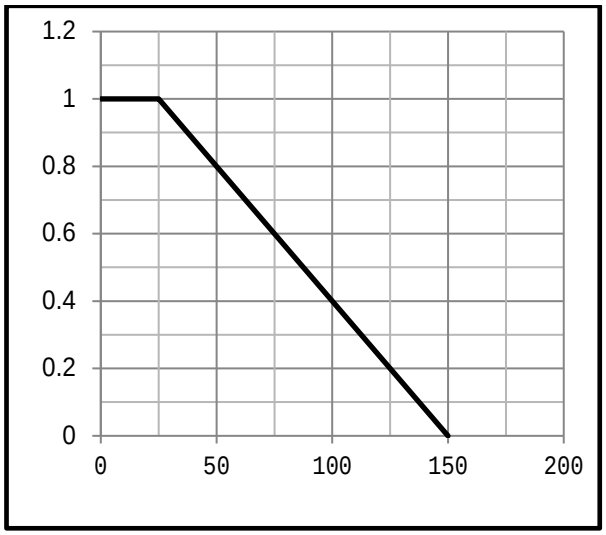


Fig.4 Typical output Characteristics

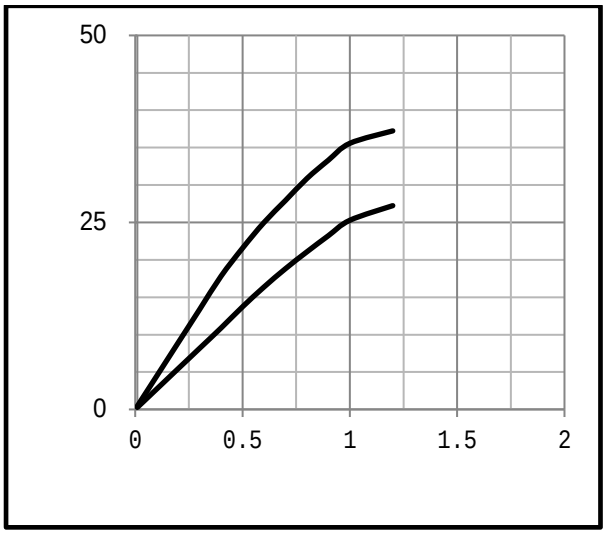


Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current

Fig.7 On-Resistance VS Gate Source Voltage

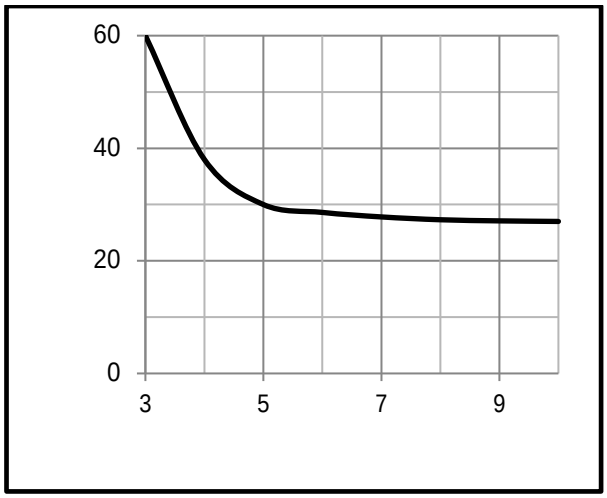


Fig.8 On-Resistance V.S Junction Temperature

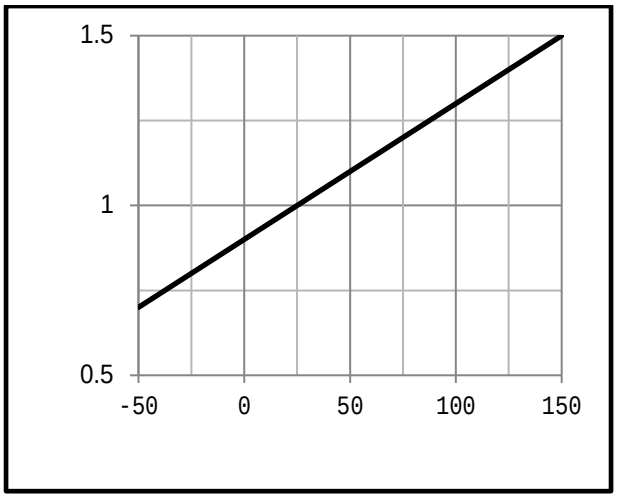


Fig.9 Switching Time Measurement Circuit

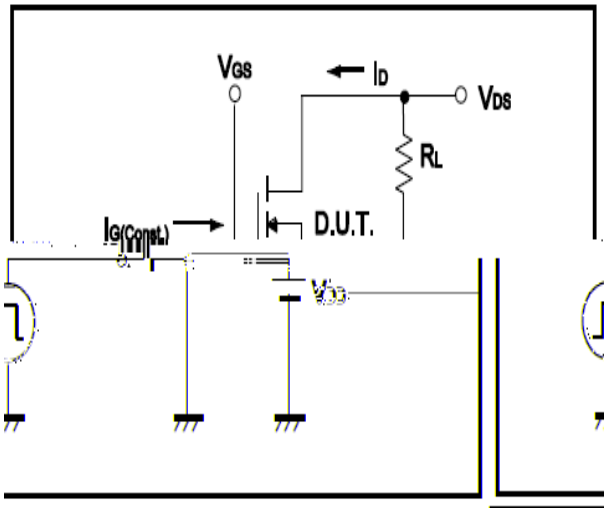


Fig.10 Gate Charge Waveform

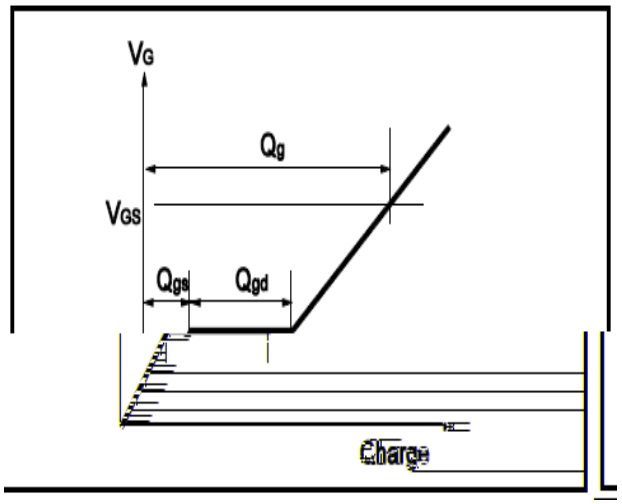


Fig.11 Switching Time Measurement Circuit

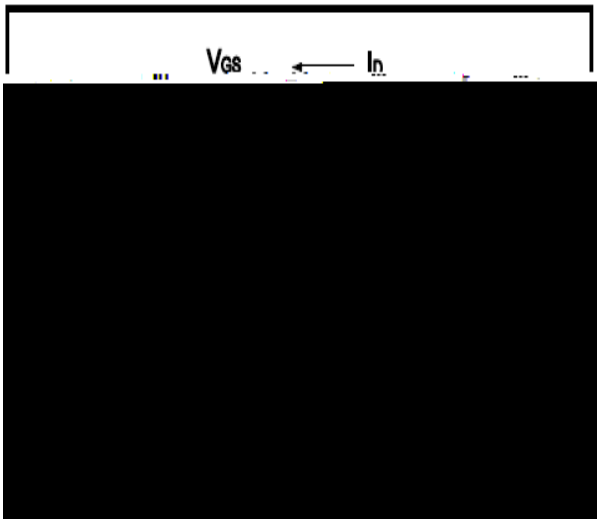


Fig.12 Gate Charge Waveform